



SI7611DN-T1-GE3 Information



For Reference Only

Part Number SI7611DN-T1-GE3
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 40V 18A 1212-8

Package PowerPAK? 1212-8

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SI7611DN-T1-GE3 Specifications

Manufacturer Part Number SI7611DN-T1-GE3 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package PowerPAK? 1212-8 Series TrenchFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 18A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 62nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1980pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.7W (Ta), 39W (Tc) Rds On (Max) @ Id, Vgs 25 mOhm @ 9.3A, 10V Operating Temperature -50°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? 1212-8 Package / Case PowerPAK? 1212-8		
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Input Capacitance (Ciss) (Max) @ Vds 1980pF @ 20V Vgs (Max) E20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 25 mOhm @ 9.3A, 10V Operating Temperature -50°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? 1212-8 Package / Case PowerPAK? 1212-8	Vgs(th) (Max) @ Id	3V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)3.7W (Ta), 39W (Tc)Rds On (Max) @ Id, Vgs25 mOhm @ 9.3A, 10VOperating Temperature-50°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? 1212-8Package / CasePowerPAK? 1212-8	Gate Charge (Qg) (Max) @ Vgs	62nC @ 10V
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Operating Temperature -50°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? 1212-8 Package / Case PowerPAK? 1212-8	Power Dissipation (Max)	3.7W (Ta), 39W (Tc)
Mounting Type Surface Mount Supplier Device Package PowerPAK? 1212-8 Package / Case PowerPAK? 1212-8	Rds On (Max) @ Id, Vgs	25 mOhm @ 9.3A, 10V
Supplier Device Package PowerPAK? 1212-8 Package / Case PowerPAK? 1212-8	Operating Temperature	-50°C ~ 150°C (TJ)
Package / Case PowerPAK? 1212-8	Mounting Type	Surface Mount
	Supplier Device Package	PowerPAK? 1212-8
Report errors?	Package / Case	PowerPAK? 1212-8
		Report errors?

SI7611DN-T1-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SI7611DN-T1-GE3 Payment Methods



















SI7611DN-T1-GE3 Shipping Methods













If you have any question about SI7611DN-T1-GE3, please do not hesitate to contact us!

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